## EFFECT OF IONIZING RADIATION ON ELECTRIC PROPERTIES OF CRYSTALLINE DIELECTRICS

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Summary

The results of experimental studies of the effect of ionizing radiation on the electric properties of crystalline dielectrics ( $\alpha$ -SiO<sub>2</sub> and  $\alpha$ -Al<sub>2</sub>O<sub>3</sub>) are presented. The regularities of thermoradiative changes in direct-current conductivity  $\sigma$ , the tangent of the angle of dielectic losses  $\operatorname{tg}\delta$ , and permittivity  $\varepsilon$  are determined, and the activation energies of the conductivity of the crystals are calculated. The approximation of the curves  $\sigma(T)$  is carried out, and the relevant laws of conductivity are revealed for both dielectrics. In the frame of the known models, the peculiarities of the kinetics of radiation-induced formation of defects and the temperature dependence of electical conduction are discussed.